

#### **Description**

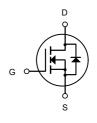
The CSD17310Q5A uses advanced trench technology to provide excellent RdS(ON), low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

DFN5X6-8L

# **General Features**

 $V_{DS} = 30V I_{D} = 60A$ 

 $R_{DS(ON)} < 7m\Omega V_{GS}=10V$ 



#### N-Channel MOSFET

# **Application**

Battery protection

Load switch

Uninterruptible power supply

## **Package Marking and Ordering Information**

Product ID	Pack	Brand	Qty(PCS)
CSD17310Q5A	DFN5X6-8L	HXY MOSFET	5000

## Absolute Maximum Ratings (Tc=25°C unless otherwise noted)

Symbol	Parameter	Rating	
V <sub>DS</sub>	Drain-Source Voltage	30	V
Vgs	Gate-Source Voltage	±20	V
I <sub>D</sub> @T <sub>C</sub> =25°C	Continuous Drain Current, Vcs @ 10V1	60	А
I <sub>D</sub> @T <sub>C</sub> =100°C	Continuous Drain Current, V <sub>GS</sub> @ 10V <sup>1</sup>	42	Α
Ірм	Pulsed Drain Current <sup>2</sup>	160	А
EAS	Single Pulse Avalanche Energy <sup>3</sup>	115.2	mJ
las	Avalanche Current	48	Α
P <sub>D</sub> @T <sub>C</sub> =25°C	Total Power Dissipation <sup>4</sup>	59	W
Тѕтс	Storage Temperature Range -55 to 150		°C
TJ	Operating Junction Temperature Range -55 to 150		°C
Reja	Thermal Resistance Junction-Ambient <sup>1</sup>	Resistance Junction-Ambient <sup>1</sup> 62	
R <sub>B</sub> JC Thermal Resistance Junction-Case <sup>1</sup>		2.1	°C/W



# Electrical Characteristics (T<sub>J</sub>=25°C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BVDSS	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V , I <sub>D</sub> =250uA	30			V
∆BVDSS/∆TJ	BVDSS Temperature Coefficient	Reference to 25°C , I <sub>D</sub> =1mA		0.028		V/°C
		V <sub>GS</sub> =10V , I <sub>D</sub> =30A		5.7	7	
RDS(ON)	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =4.5V , I <sub>D</sub> =15A		11	13	$m\Omega$
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =250uA	1.2		2.5	V
$\triangle V_{GS(th)}$	V <sub>GS(th)</sub> Temperature Coefficient	VGS-VDS, ID-250UA		-6.16		mV/°C
loss	Drain-Source Leakage Current	V <sub>DS</sub> =24V , V <sub>GS</sub> =0V , T <sub>J</sub> =25°C			1	
1033	Diam-Source Leakage Surrem	V <sub>DS</sub> =24V , V <sub>GS</sub> =0V , T <sub>J</sub> =55°C			5	uA
Igss	Gate-Source Leakage Current	$V_{GS}$ = $\pm 20V$ , $V_{DS}$ = $0V$			±100	nA
gfs	Forward Transconductance	$V_{DS}$ =5 $V$ , $I_{D}$ =30 $A$		43		S
Rg	Gate Resistance	V <sub>DS</sub> =0V , V <sub>GS</sub> =0V , f=1MHz		1.7		Ω
Qg	Total Gate Charge (4.5V)			20		
Qgs	Gate-Source Charge	V <sub>DS</sub> =15V , V <sub>GS</sub> =4.5V , I <sub>D</sub> =15A		7.6		nC
Q <sub>gd</sub>	Gate-Drain Charge			7.2		
Td(on)	Turn-On Delay Time			7.8		
Tr	Rise Time	V <sub>DD</sub> =15V , V <sub>GS</sub> =10V ,		15		ns
T <sub>d(off)</sub>	Turn-Off Delay Time	$-R_{G}=3.3\Omega$		37.3		
Tf	Fall Time	I <sub>D</sub> =15A		10.6		
Ciss	Input Capacitance			2295		
Coss	Output Capacitance	V <sub>DS</sub> =15V , V <sub>GS</sub> =0V , f=1MHz		267		pF
Crss	Reverse Transfer Capacitance			210		'
ls	Continuous Source Current <sup>1,5</sup>				81	Α
lsм	Pulsed Source Current <sup>2,5</sup>	V <sub>G</sub> =V <sub>D</sub> =0V , Force Current			160	Α
VsD	Diode Forward Voltage <sup>2</sup>	V <sub>GS</sub> =0V , I <sub>S</sub> =1A , T <sub>J</sub> =25°C			1	V
t <sub>rr</sub>	Reverse Recovery Time	100 37 , 10 11.1, 10 20 0		14		nS
Qrr	Reverse Recovery Charge	IF=30A, dI/dt=100A/μs , T <sub>J</sub> =25°C		5		nC

#### Note:

<sup>1.</sup> The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper.

<sup>2.</sup>The data tested by pulsed , pulse width  $\leq$  300us , duty cycle  $\leq$  2%

<sup>3.</sup> The EAS data shows Max. rating . The test condition is  $V_{DD}$ =25V,  $V_{GS}$ =10V,L=0.1mH,  $I_{AS}$ =48A

<sup>4.</sup> The power dissipation is limited by 150°C junction temperature

<sup>5.</sup> The data is theoretically the same as  $I_D$  and  $I_{DM}$ , in real applications, should be limited by total power dissipation.



# **Typical Characteristics**

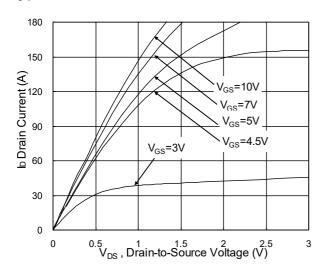


Fig.1 Typical Output Characteristics

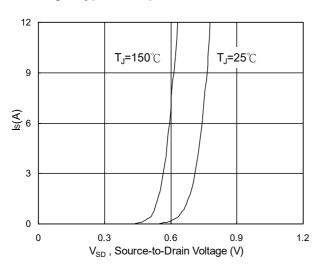


Fig.3 Forward Characteristics of Reverse

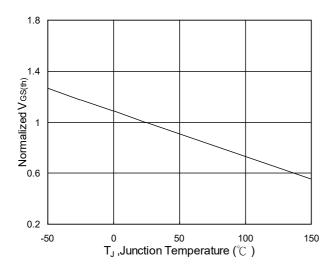


Fig.5 Normalized  $V_{\text{GS(th)}}$  vs.  $T_{\text{J}}$ 

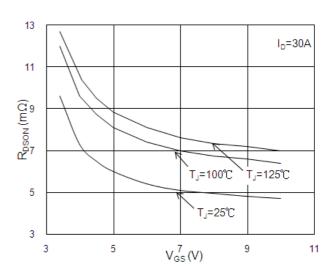


Fig.2 On-Resistance vs. G-S Voltage

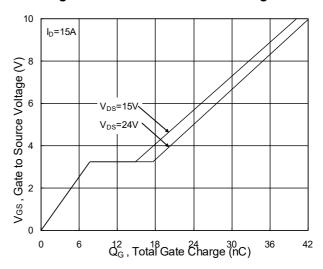


Fig.4 Gate-Charge Characteristics

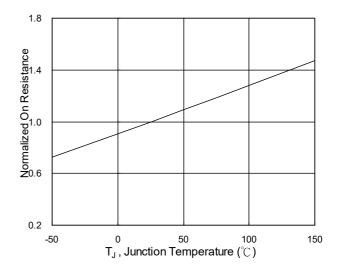
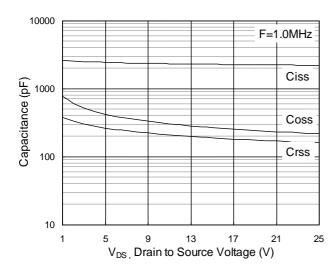


Fig.6 Normalized R<sub>DSON</sub> vs. T<sub>J</sub>



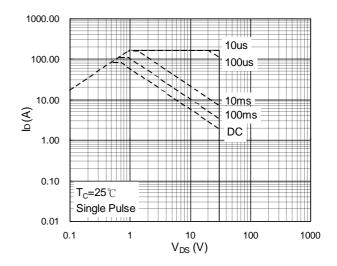


Fig.7 Capacitance

Fig.8 Safe Operating Area

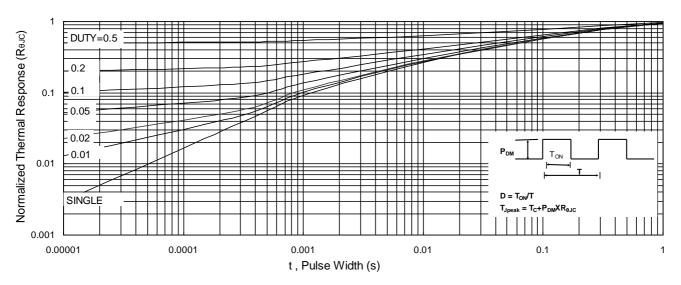


Fig.9 Normalized Maximum Transient Thermal Impedance

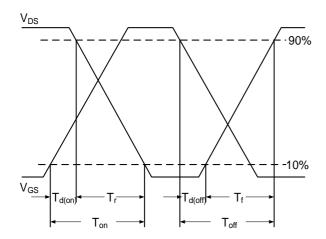


Fig.10 Switching Time Waveform

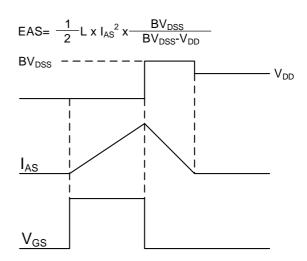
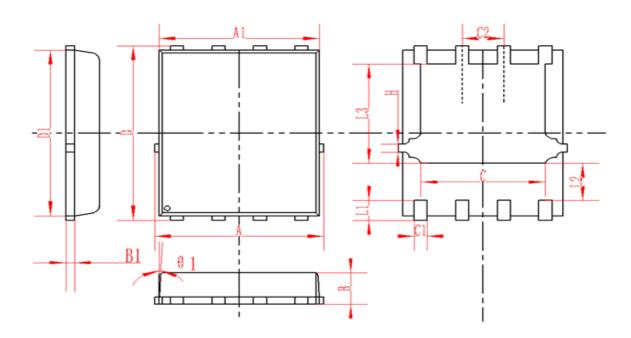


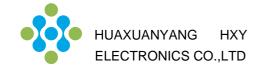
Fig.11 Unclamped Inductive Switching Waveform



# **DFN5X6-8L Package Information**



SYMBOL	MM		INCH			
	MIN	NOM	MAX	MIN	NOM	MAX
А	4.95	5	5.05	0.195	0.197	0.199
A1	4.82	4.9	4.98	0.190	0.193	0.196
D	5.98	6	6.02	0.235	0.236	0.237
D1	5.67	5.75	5.83	0.223	0.226	0.230
В	0.9	0.95	1	0.035	0.037	0.039
B1	0.254REF		0.010REF			
С	3.95	4	4.05	0.156	0.157	0.159
C1	0.35	0.4	0.45	0.014	0.016	0.018
C2		1.27TYP			0.5TYP	
θ1	8°	10°	12°	8°	10°	12°
L1	0.63	0.64	0.65	0.025	0.025	0.026
L2	1.2	1.3	1.4	0.047	0.051	0.055
L3	3.415	3.42	3.425	0.134	0.135	0.135
Н	0.24	0.25	0.26	0.009	0.010	0.010



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